

# FDT86113LZ

## N-Channel PowerTrench® MOSFET

100 V, 3.3 A, 100 mΩ

### Features

- Max  $r_{DS(on)}$  = 100 mΩ at  $V_{GS} = 10$  V,  $I_D = 3.3$  A
- Max  $r_{DS(on)}$  = 145 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 2.7$  A
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- HBM ESD protection level > 3 KV typical (Note 4)
- 100% UIL tested
- RoHS Compliant

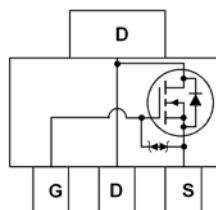
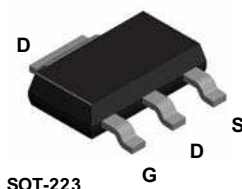


### General Description

This N-Channel logic Level MOSFETs are produced using Fairchild Semiconductor's advanced Power Trench® process that has been special tailored to minimize the on-state resistance and yet maintain superior switching performance. G-S zener has been added to enhance ESD voltage level.

### Application

- DC - DC Switch



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	3.3	A
	-Pulsed	12	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	9	mJ
$P_D$	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.2	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1b)	1.0	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	12	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	55	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
86113LZ	FDT86113LZ	SOT-223	13 "	12 mm	2500 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		71		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\ \text{V}$ , $V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}$ , $V_{DS} = 0\ \text{V}$			$\pm 10$	$\mu\text{A}$

**On Characteristics (Note 2)**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$	1.0	1.7	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 3.3\ \text{A}$		75	100	m $\Omega$
		$V_{GS} = 4.5\ \text{V}$ , $I_D = 2.7\ \text{A}$		95	145	
		$V_{GS} = 10\ \text{V}$ , $I_D = 3.3\ \text{A}$ , $T_J = 125^\circ\text{C}$		140	189	
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\ \text{V}$ , $I_D = 3.3\ \text{A}$		8		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$		234	315	pF
$C_{oss}$	Output Capacitance			46	65	pF
$C_{rss}$	Reverse Transfer Capacitance			3.1	5	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\ \text{V}$ , $I_D = 3.3\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$		3.8	10	ns
$t_r$	Rise Time			1.3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			10	20	ns
$t_f$	Fall Time			1.5	10	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $10\ \text{V}$	$V_{DD} = 50\ \text{V}$ , $I_D = 3.3\ \text{A}$	4.1	6.8	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $5\ \text{V}$		2.3	3.9	nC
$Q_{gs}$	Gate to Source Gate Charge			0.68		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			0.85		nC

**Drain-Source Diode Characteristics**

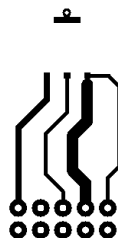
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}$ , $I_S = 3.3\ \text{A}$ (Note 2)		0.86	1.3	V
		$V_{GS} = 0\ \text{V}$ , $I_S = 1\ \text{A}$ (Note 2)		0.77	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 3.3\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$		31	49	ns
$Q_{rr}$	Reverse Recovery Charge			21	34	nC

Notes:

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a)  $55^\circ\text{C}/\text{W}$  when mounted on a  
1 in<sup>2</sup> pad of 2 oz copper



b)  $118^\circ\text{C}/\text{W}$  when mounted on  
a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3. Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.3\ \text{mH}$ ,  $I_{AS} = 8\ \text{A}$ ,  $V_{DD} = 90\ \text{V}$ ,  $V_{GS} = 10\ \text{V}$ .

4. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

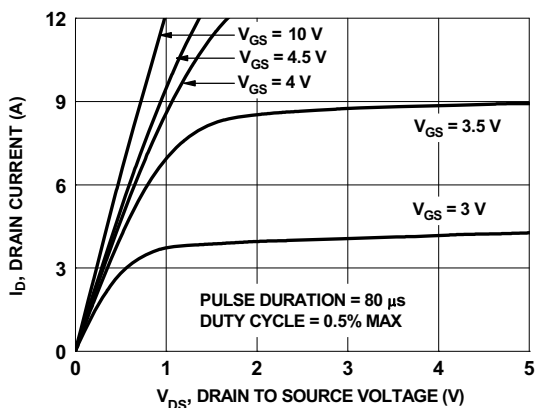


Figure 1. On-Region Characteristics

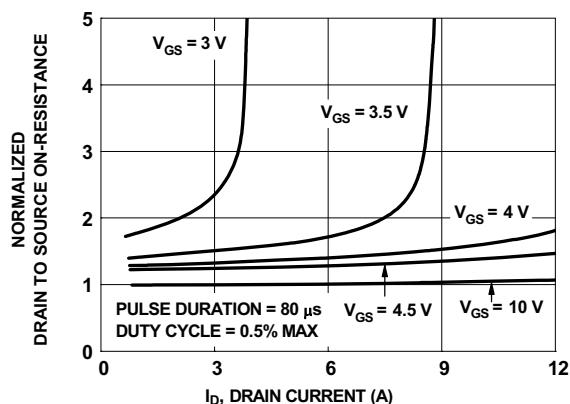


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

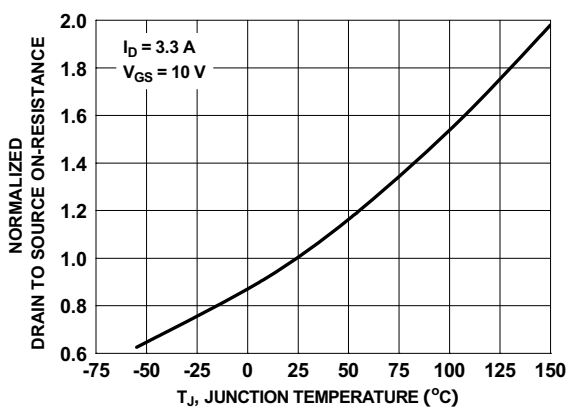


Figure 3. Normalized On-Resistance vs Junction Temperature

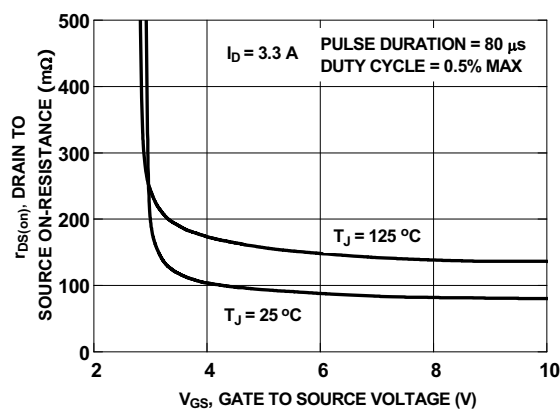


Figure 4. On-Resistance vs Gate to Source Voltage

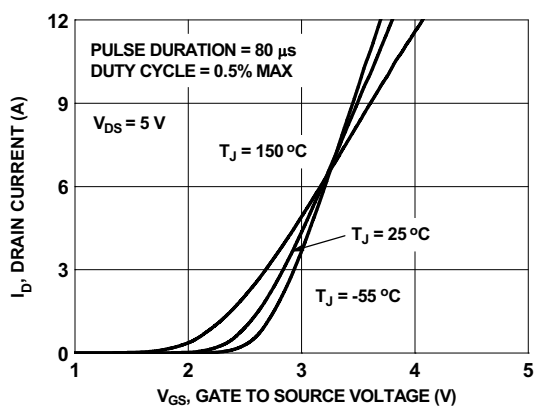


Figure 5. Transfer Characteristics

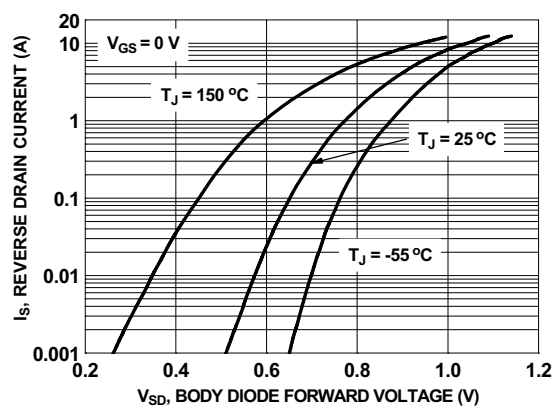


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

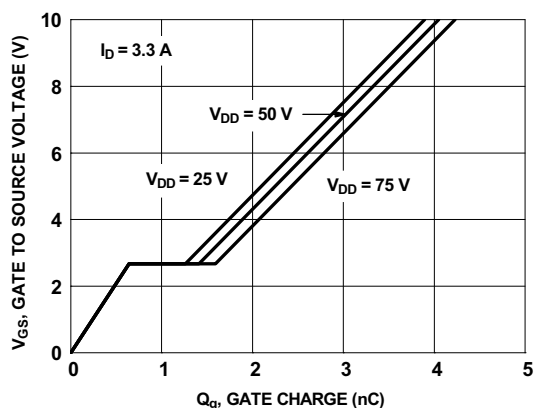


Figure 7. Gate Charge Characteristics

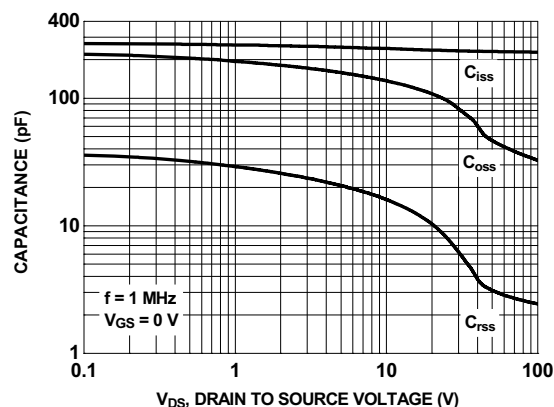


Figure 8. Capacitance vs Drain to Source Voltage

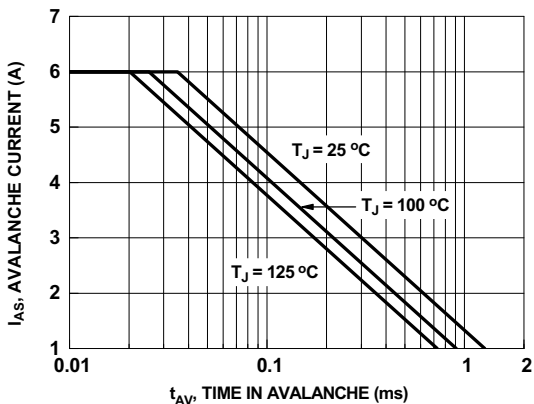


Figure 9. Unclamped Inductive Switching Capability

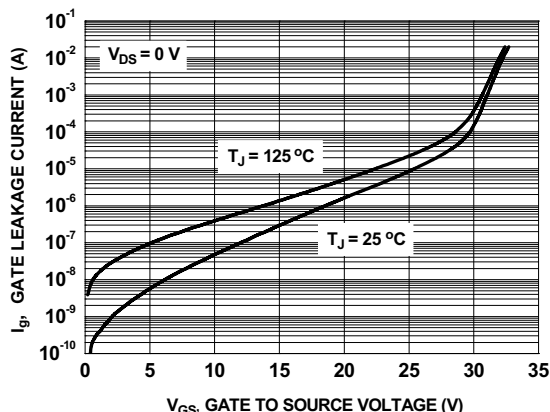


Figure 10. Gate Leakage Current vs Gate to Source Voltage

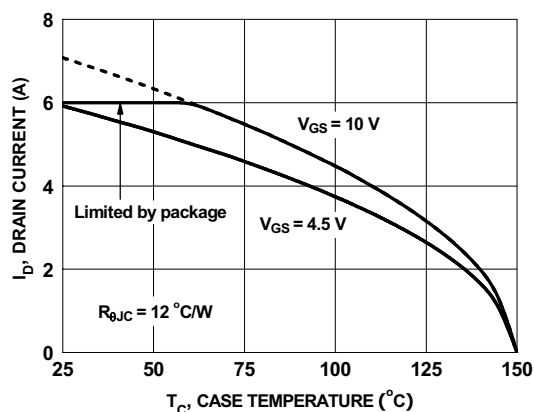


Figure 11. Maximum Continuous Drain Current vs Case Temperature

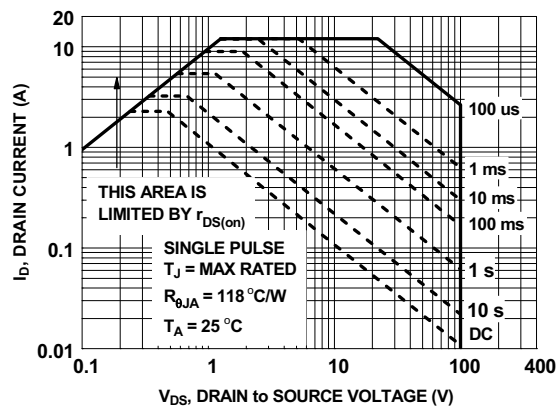


Figure 12. Forward Bias Safe Operating Area

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

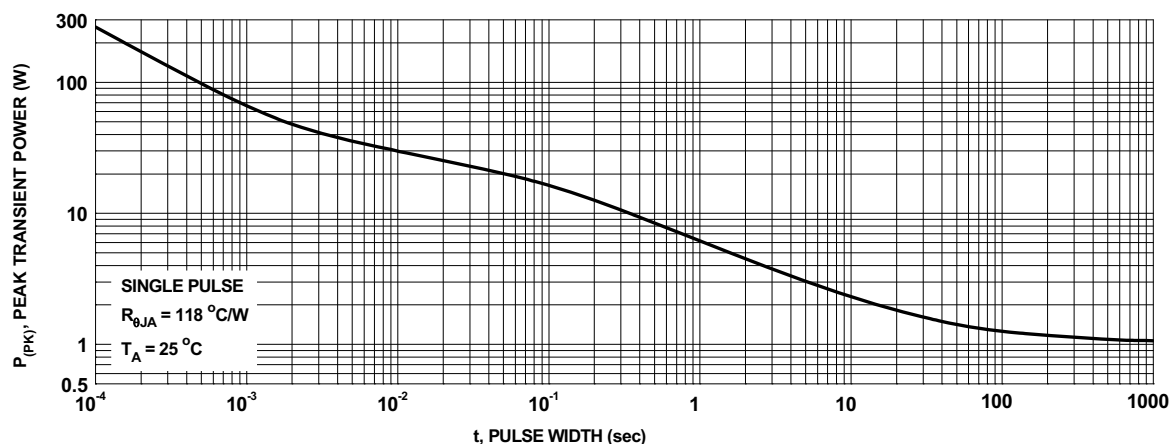


Figure 13. Single Pulse Maximum Power Dissipation

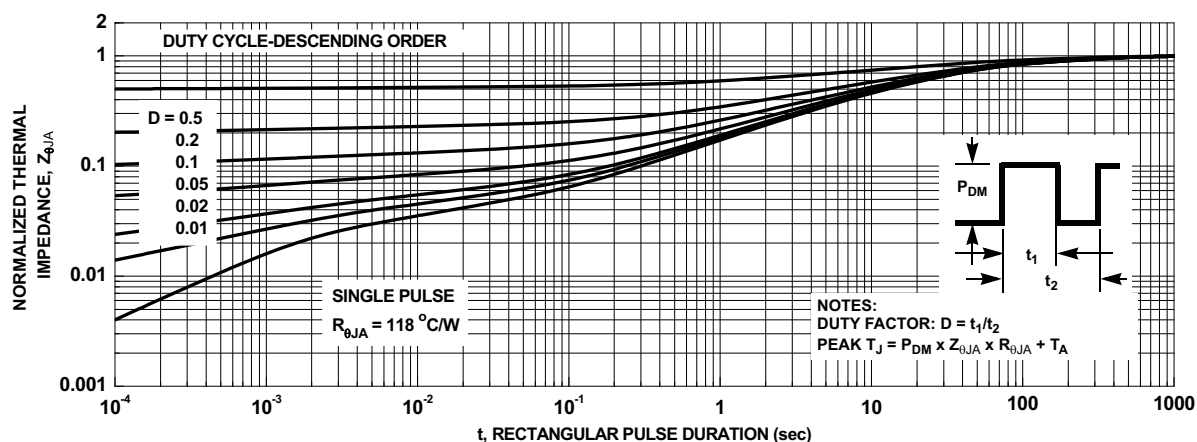



Figure 14. Junction-to-Ambient Transient Thermal Response Curve

AccuPower™  
Auto-SPM™  
AX-CAP™\*  
Build it Now™  
CorePLUS™  
CorePOWER™  
CROSSVOLT™  
CTL™  
Current Transfer Logic™  
DEUXPEED®  
Dual Cool™  
EcoSPARK™  
EfficientMax™  
ESBC™  
**F**®  
Fairchild®  
Fairchild Semiconductor®  
FACT Quiet Series™  
FACT®  
FAST®  
FastvCore™  
FETBench™  
FlashWriter®\*  
FPS™


F-PFS™  
FRFET®  
Global Power Resource SM  
Green FPS™  
Green FPS™ e-Series™  
Gmax™  
GTO™  
IntelliMAX™  
ISOPLANAR™  
MegaBuck™  
MICROCOUPLER™  
MicroFET™  
MicroPak™  
MicroPak2™  
MillerDrive™  
MotionMax™  
Motion-SPM™  
mWSaver™  
OptiHit™  
OPTOLOGIC®  
OPTOPLANAR®  
  
PDP SPM™

Power-SPM™  
PowerTrench®  
PowerXS™  
Programmable Active Droop™  
QFET®  
QS™  
Quiet Series™  
RapidConfigure™  
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SignalWise™  
SmartMax™  
SMART START™  
SPM®  
STEALTH™  
SuperFET®  
SuperSOT™\_3  
SuperSOT™\_6  
SuperSOT™\_8  
SupreMOS®  
SyncFET™  
Sync-Lock™  
SYSTEM  
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The Right Technology for Your Success<sup>™</sup>

**power**  
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TinyBuck<sup>™</sup>  
TinyCalc<sup>™</sup>  
TinyLogic<sup>®</sup>  
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TinyPWM<sup>™</sup>  
TinyWire<sup>™</sup>  
TriFault Detect<sup>™</sup>  
TRUECURRENT<sup>®</sup>\*  
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 SerDes<sup>™</sup>

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